PATENT Attorney Docket No.: MLB-066C2



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

APPLICANT:

Griffith et al.

SERIAL NO.:

10/646,146

GROUP NO.:

Not Yet Assigned

FILING DATE:

August 22, 2003

EXAMINER:

Not Yet Assigned

TITLE:

METHODS AND APPARATUS FOR MANUFACTURING ELECTRONIC

AND ELECTROMECHANICAL ELEMENTS AND DEVICES BY THIN-FILM

DEPOSITION AND IMAGING

CERTIFICATE OF FIRST CLASS MAILING UNDER 37 C.F.R. 1.8

I hereby certify that this correspondence, and any document(s) referred to as enclosed herein, is/are being deposited with the United States Postal Service as first class mail, postage prepaid, in an envelope addressed to the Commissioner for Patents, P.O. Box 1450, Alexandria VA 22313-1450 on this 10th day of December, 2003.

Anna-Karin Kuliga

Commissioner for Patents P.O. Box 1450 Alexandria VA 22313-1450

Sir:

Submitted herewith are:

- 1. Transmittal Form (1 page);
- 2. Information Disclosure Statement (2 pages);
- 3. Form PTO-1449 (3 pages); and
- 4. References cited (A1-A6, B1 and C1-C39); and
- 5. Return receipt postcard.

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1	1 2 2003		Application	Serial Number		10/646,146			
(DE		Filing Date			August 22, 2003				
1 PER	ark		First Named Inventor			Griffith			
	TRANSMITTA	Ι.	Group Art U	Jnit		Not Yet Assigned			
			Examiner Name			Not Yet Assigned			
	FORM		Attorney Do	ocket No.		MLB-066C2			
		Patent No.				Not applicable			
			Issue Date			Not applicable			
		EN	CLOSURES (c	heck all that apply)					
☐ Fe	ee Transmittal Form		Copy of Notic	e to File Missing cation (PTO-1553)		Notice of Appeal to Board of Patent Appeals and Interferences			
	☐ Check Attached☐ Copy of Fee Transmittal Form		Formal Drawin	, , ,					
	Amendment/Response		Request For Continued Examination (RCE) Transmittal		ב	Status Inquiry			
	☐ Preliminary ☐ After Final	_				Return Receipt Postcard			
	☐ Affidavits/declaration(s) ☐ Letter to Official ☐ Draftsperson		Power of Attor (Revocation of	rney f Prior Powers)	Þ	Certificate of First Class Mailing under 37 C.F.R. 1.8			
	including Drawings [Total Sheets]		Terminal Disclaimer			Certificate of Facsimile Transmission under 37 C.F.R. 1.8			
	Petition for Extension of Time			aration and Power r Utility or Design ttion		Additional Enclosure(s) (please identify below)			
Information Disclosure Statement			Small Entity S	tatement					
	Form PTO-1449 Copies of IDS		CD(s) for large	e table or computer					
	Certified Copy of Priority Document(s)		Amendment After Allowance						
	Sequence Listing submission Paper Copy/CD Computer Readable Copy Statement verifying identity of above		Request for Co Correction Certificate duplicate)	ertificate of of Correction (in					
CORR	ESPONDENCE ADDRESS			SIGNATURE BLO	oc				
Direct	Testa, Hu High Stre 125 High Boston, M Tel. No.:	et Tower	nibeault, LLP	Date: December 10, 2003 Reg. No. 45,054 Tel. No.: (617) 248-7376 Fax No.: (617) 248-7100 Attorney for the Applicant Testa, Hurwitz & Thibeault, LLP High Street Tower 125 High Street Boston, MA 02110					

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Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

INFORMATION DISCLOSURE STATEMENT

Sir:

In accordance with the provisions of 37 C.F.R. 1.97 and 1.98, Applicants hereby make of record the patents and publications listed on the accompanying Form PTO-1449, and other information contained herein, for consideration by the Examiner in connection with the examination of the above-identified patent application. Copies of the patents and publications are enclosed.

REMARKS

In accordance with the provisions of 37 C.F.R. 1.97, this statement is being filed (CHECK ONE):

(1)	within three (3) months of the filing date of a national application other than a continued prosecution application under 37 C.F.R. 1.53(d), or within three (3) months of the date of entry of the national stage as set forth in 37 C.F.R. 1.491 in an international application, or before the mailing of the first Office action on the merits, or before the mailing of a first Office action after the filing of a request for continued examination under 37 C.F.R. 1.114; or
(2)	after the period defined in (1) but before the mailing date of a final action or a notice of allowance under 37 C.F.R. 1.311, and
	the requisite Statement is below, OR
	the requisite fee under 37 C.F.R. 1.17(p), namely \$180.00, is included herein, or

	(3		after the mailing date of a final action or notice of allowance but before the payment of the issue fee, AND
] t	he requisite Statement is below, AND
] t	he requisite petition fee under 37 C.F.R. 1.17(p), namely \$180.00 is included herein.
	-		ly requested that each of the patents and publications listed on the attached Form er information contained herein, be made of record in this application.
			STATEMENT
A	As requi	red un	nder 37 C.F.R. 1.97(e), Applicant(s), through the undersigned, hereby state either that
[checl	k the ap	propi	riate space only if either (2) or (3) is checked on the previous page <u>and</u> the
Stater	nent is 1	requi	red]:
		1.	Each item of information contained in the Information Disclosure Statement was first cited in any communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of the Information Disclosure Statement; or
		2.	No item of information contained in the Information Disclosure Statement was cited in a communication from a foreign patent office in a counterpart foreign application, and, to the knowledge of the person signing this Statement after making reasonable inquiry, no item of information contained in the Information Disclosure Statement was known to any individual designated in 37 C.F.R. 1.56(c) more than three months prior to the filing of the Information Disclosure Statement.
Date:	Decemb	er 10,	Respectfully submitted,

Tel. No.: (617) 248-7376 Fax No.: (617) 248-7100

Reg. No. 45,054

Attorney for Applicants
Testa, Hurwitz, & Thibeault, LLP

High Street Tower 125 High Street

Jamie H. Rose

Boston, Massachusetts 02110

FORM PTO - 14 TRADESINFORMATION DISCLOSURE STATEMENT

ATTORNEY DOCKET NO.: MLB-066C2

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FILING DATE: August 22, 2003 GROUP: Not Yet Assigned

		·		FILII	NG DATE	: August 2	22, 2003 (JROUP: N	Not Y	et Assigned	
			U.S.	PATENT I	OCUME	ENTS					
EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	NAME			CLASS SUB CLASS		FILING DATE IF APPROPRIATE	
	A1	4,298,448	11/03/81	Muller et a	ıl.						
	A2	5,066,559	11/19/91	Elmasry et	al.						
	A3	5,380,362	01/10/95	Schubert	Schubert						
	A4	5,559,057	09/24/96	Goldstein							
	A5	5,587,111	12/24/96	Watanabe	Watanabe et al.						
	A6	5,751,018	05/12/98	Alivisatos	et al.						
			FOREI	GN PATEN	T DOCU	MENTS					
EXAM. INIT.		DOCUMENT NUMBER	DATE	COUNTRY CODE	CLASS	SUB CLASS	FILING DATE	ABSTRA ONLY	СТ	ENGLISH LANG (Y/N)	
V	Bl	WO 97/38810	10/23/97	PCT				N		Y	
-		(OTHER AF	RT, JOURNA	AL ARTI	CLES, E	TC.	<u> </u>		·	
EXAM. INIT.	OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)										
V	C1	Guo et al., "A Room-Temperature Silicon Single-Electron Metal-Oxide-Semiconductor Memory With Nanoscale Floating-Gate and Ultranarrow Channel," Appl. Phys. Lett. 70 (7), pp. 850-852, February 17, 1997.									
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v	C4	Yano et al., "SA 21.7:A 128 Mb Early Prototype for Gigascale Single-Electron Memories," IEEE International Solid-State Circuits Conference, 1998.									
V	C5	Ishii et al., "Verify: Key to the Stable Single-Electron-Memory Operation," IEEE, IEDM 97, pp. 171-174, 1997.									
V	C6	Yano et al., "FP 16.4: Single-Electron-Memory Integrated Circuit for Giga-to-Tera Bit Storage," IEEE International Solid-State Circuits Conference, 1996.									
V	C7	C7 Nakajima et al., "Room Temperature Operation of Si Single-Electron Memory with Self-Aligned Floating Dot Gate," IEDM 96, pp. 952-954, 1996.									
	C8 Tiwari et al., "Technology and Power-Speed Trade-Offs in Quantum-Dot and Nano-Crystal Memory Devices," Symposium on VLSI Technology Digest of Technical Papers, pp. 133-134, 1997.										

FORM PTO - 1949
INFORMATION DISCLOSURE
STATEMENT

ATTORNEY DOCKET NO.: MLB-066C2

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			FILING DATE: August 22, 2003 GROUP: Not Yet Assigned			
V	C9	Bhyrappa et al., "Hydrogen-Bonded Porphyrinic Solids: Supramolecular Networks of Octahydroxy Porphyrins," J. Am. Chem. Soc., Vol. 119, 8492-8502, 1997.				
V	C10	Zollinger, Color Chemistry, 2 nd Ed., Weinheim, New York, pp. 352-361, 1991.				
i	C11	Murray et al., "Self-Organization of CdSe Nanocrystallites Into Three-Dimensional Quantum Dot Superlattices," Science, Vol. 270, pp. 1335-1338, November 24, 1995.				
υ	C12	Terris et al., "Near-Field Optical Data No. 4, pp. 388-390, July 25, 1994.	Storage Using a Solid Immersion Lens," Appl. Phys. Lett., Vol. 65,			
V	C13	Markovich et al., "Parallel Fabrication and Single-Electron Charging of Devices Based on Ordered, Two-Dimensional Phases of Organically Functionalized Metal Nanocrystals," Appl. Phys. Lett. 70 (23), pp. 3170-3109, June 9, 1997.				
v	C14	Yoo et al., "Scanning Single-Electron Transistor Microscopy: Imaging Individual Charges," Science, Vol. 276, pp. 579-582, April 25, 1997.				
i	C15	Schoelkopf et al., "The Radio-Frequency Single-Electron Transistor (RF-SET): A Fast and Ultrasensitive Electrometer," Science, Vol. 280, pp. 1238-1242, May 22, 1998.				
ν	C16	Shum et al., "A Concept for Nonvolatile Memories," Appl. Phys. Lett., 71 (17), pp. 2487-2489, October 27, 1997.				
V	C17	Tayaoka et al., "Preparation of Co-Fe-P Amorphous Fine Needles With Anodization Technique and Measurement of Demagnetizing Factor," J. Appl. Phys. 79 (8), pp. 6016-6018, April 15, 1996.				
υ	C18	Meier et al., "Magnetic Properties of Nanosized Wires," J. Appl. Phys. 79 (8), pp. 6010-6012, April 15, 1996.				
v	C19	Lafdi et al., "Cobalt-Doped Carbon Nanotubes: Preparation, Texture, and Magnetic Properties," J. Appl. Phys. 79 (8), pp. 6007-6009, April 15, 1996.				
i	C20	Mamin et al., "High-Density Data Storage Using Proximal Probe Techniques," IBM J. Res. Develop., Vol. 39, No. 6, pp. 681-699, November 6, 1995.				
v	C21	Masumoto et al., "Room Temperature Operation of a Single Electron Transistor Made by the Scanning Tunneling Microscope Nanooxidation Process for the TiOx/Ti System," Appl. Phys. Lett., 68 (1), pp. 34-36, January 1, 1996.				
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U	C23	Snow et al., "A Metal/Oxide Tunneling Transistor," Appl. Phys. Lett., 72 (23), pp. 3071-3073, June 8, 1998.				
J	C24	Minne et al., "Automated Parallel High-Speed Atomic Force Microscopy," Appl. Phys. Lett., 72 (18), pp. 2340-2342, May 4, 1998.				
1	C25	Celotta et al., "Nanostructure Fabrication Via Laser-Focused Atomic Deposition (Invited)," J. Appl. Phys. 79 (8), pp. 6079-6083, April 15, 1996.				
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		N DISCLOSURE	APPLICANT(S): Griffith et al. SERIAL NO.: 10/646,146				
STATEM	IENT						
			FILING DATE: August 22, 2003 GROUP: Not Yet Assigned				
V	C27	Doudin et al., "Arrays of Multilayere 15, 1996.	d Nanowires (Invited)," J. Appl. Phys. 79 (8), pp. 60909-6094, April				
٧	C28	Gadetsky et al., "Magneto-Optical Re 5687-5692, April 15, 1996.	ecording on Patterned Substrates (Invited)," J. Appl. Phys. 79 (8), pp.				
V	C29	Bessho et al., "Fabricating Nanoscale Phys. 79 (8), pp. 5057-5059, April 1:	e Magnetic Mounds Using a Scanning Probe Microscope," J. Appl. 5, 1996.				
V	C30	Leslie-Pelecky et al., "Self-Stabilized Phys. 79 (8), pp. 5312-5314, April 1	Magnetic Colloids: Ultrafine CO particles in Polymers," J. Appl. 5, 1996.				
v	C31	Johnson et al., "Finite Size Effects in Nanoscale Tb Particles," J. Appl. Phys. 79 (8), pp. 5299-5301, April 15, 1996.					
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/	C33	Levy et al., "Femtosecond Near-Field Spin Microscopy in Digital Magnetic Heterostructures (Invited)," J. Appl. Phys. 79 (8), pp. 6095-6100, April 15, 1996.					
ν	C34	Chou et al., "65 Gbits/in.2 Quantum Magnetic Disk (Abstract)," J. Appl. Phys. 79 (8), p. 5066, April 15, 1996.					
∠/	C35	Chou et al., "Nanolithographically Defined Magnetic Structures and Quantum Magnetic Disk (Invited)," J. Appl. Phys. 79 (8), pp. 6101-6106, April 15, 1996.					
J	C36	Alivisatos, "Electrical Studies of Semiconductor-Nanocrystal Colloids," MRS Bulletin, pp. 18-23, February 1998.					
V	C37	Xia et al., "Soft Lithography," Angew. Chem. Int. Ed., Vol. 37, pp. 551-575, 1998.					
V	C38	Rosa et al., Direct Patterning of Surface Quantum Wells With An Atomic Force Microscope," Appl. Phys. Lett., 73 (18), pp. 2684-2686, November 2, 1998.					
U	C39	Schamp et al., "Improved efficiencies in light emitting diodes made with CdSe (CdS) core/shell type nanocrystals and a semiconducting polymer," J. Appl. Phys., 82 (11), pp, 5837-5842, December 1, 1997.					
EXAMINER			DATE CONSIDERED				

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